

METHOD OF FORMING INTER-DIELECTRIC LAYER IN SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

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The present invention relates to a method of forming an interlayer dielectric film in a semiconductor device. More particularly, the present invention selectively forms an insulating film spacer only at a region where a plug is formed between metal lines and removes the insulating film spacer at a
10 region where the plug is not formed to lower the aspect ratio between the metal lines, in a process of burying an insulating material between the metal lines to electrically insulate them. Therefore, the present invention can easily bury the insulating material even between the metal lines having a narrow gap without voids.